

Differential Hall Effect Sensor IC in CMOS technology

Release Notes: Revision bars indicate significant changes to the previous edition.

Features:

- distance between Hall plates: 2.05 mm
- operates from 4.5 V to 24 V supply voltage
- overvoltage and reverse-voltage protection
- short-circuit protected open-drain output
- operates with magnetic fields from DC to 10 kHz
- switching offset compensation at 57 kHz
 - output turns low with magnetic south pole on branded side of package and with a higher magnetic flux density in sensitive area S1 as in S2
 - output state does not change if magnetic field is removed
 - on-chip temperature compensation circuitry minimizes shifts in on and off points and hysteresis over temperature and supply voltage
 - the decrease of magnetic flux density caused by rising temperature in the sensor system is compensated by a built-in negative temperature coefficient of hysteresis
 - ideal sensor for ignition timing, anti-lock brake systems and revolution counting with rotating magnets in extreme automotive and industrial environments
 - EMC corresponding to DIN 40839

Marking Code

Туре	Temperature Range			
	А	E	С	
HAL300S, HAL300UA	300A	300E	300C	

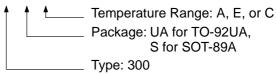
Operating Junction Temperature Range

A: $T_J = -40 \text{ °C to } +170 \text{ °C}$ **E:** $T_J = -40 \text{ °C to } +100 \text{ °C}$

C: $T_J = 0 \ ^{\circ}C$ to +100 $^{\circ}C$

Designation of Hall Sensors





Example: HAL300UA-E

- \rightarrow Type: 300
- \rightarrow Package:TO-92UA
- \rightarrow Temperature Range: T_J = -40 °C to +100 °C

Solderability

- Package SOT-89A: according to IEC68-2-58
- Package TO-92UA: according to IEC68-2-20

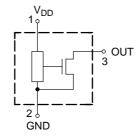


Fig. 1: Pin configuration

Functional Description

This Hall effect sensor is a monolithic integrated circuit that switches in response to differential magnetic fields. If magnetic fields with flux lines at right angles to the sensitive areas are applied to the sensor, the biased Hall plates forces Hall voltages proportional to this fields. The difference of the Hall voltages is compared with the actual threshold level in the comparator. The temperature-dependent bias increases the supply voltage of the Hall plates and adjusts the switching points to the decreasing induction of magnets at higher temperatures. If the differential magnetic field exceeds the threshold levels, the open drain output switches to the appropriate state. The built-in hysteresis eliminates oscillation and provides switching behavior of output without bounce.

Magnetic offset is compensated for by using the "switching offset compensation technique". Therefore, an internal oscillator provides a two phase clock. The difference of the Hall voltages are sampled at the end of the first phase. At the end of the second phase, both sampled and momentary differential Hall voltages are averaged and compared with the actual switching point. Subsequently, the open drain output switches to the appropriate state. The time from crossing the magnetic switch level to switching of output can vary between zero and $1/f_{osc}$.

Shunt protection devices clamp voltage peaks at the Output-Pin and V_{DD}-Pin together with external series resistors. Reverse current is limited at the V_{DD}-Pin by an internal series resistor up to -15 V. No external reverse protection diode is needed at the V_{DD}-Pin for values ranging from 0 V to -15 V.

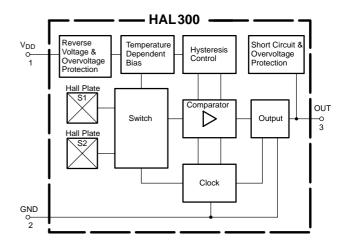


Fig. 2: HAL300 block diagram

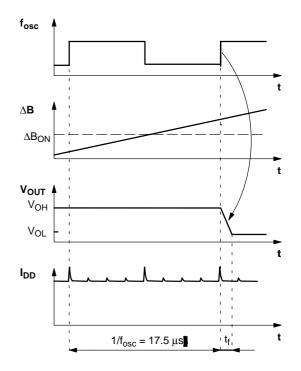


Fig. 3: Timing diagram

Outline Dimensions

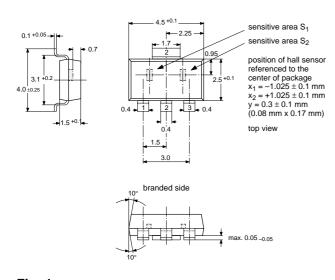


Fig. 4: Plastic Small Outline Transistor Package (SOT-89A) Weight approximately 0.04 g Dimensions in mm

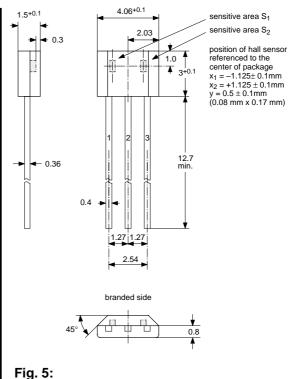


Fig. 5: Plastic Transistor Single Outline Package (TO-92UA) Weight approximately 0.12 g Dimensions in mm

Absolute Maximum Ratings

Symbol	Parameter	Pin No.	Min.	Max.	Unit
V _{DD}	Supply Voltage	1	–15 –24 ²⁾	28 ¹⁾	V
V _{OH}	Output Off Voltage	3	_	28 ¹⁾	V
l _O	Continuous Output On Current	3	_	30	mA
l _O	Peak Output On Current	3	_	250 ³⁾	mA
-I _{DD}	Reverse Supply Current	1		50 ¹⁾	mA
I _{DDZ}	Supply Current through Protection Diode	1	-300	300 ³⁾	mA
Ts	Storage Temperature Range		-65	150	°C
TJ	Junction Temperature Range		-40 -40	150 170 ⁴⁾	°C

¹⁾ as long as T_Jmax is not exceeded

²⁾ with a 220 Ω series resistance at pin 1 corresponding to test circuit 1

³⁾ t < 2 ms

⁴⁾ t < 1000 h

Stresses beyond those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions/Characteristics" of this specification is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

Recommended Operating Conditions

	Symbol	Parameter	Pin No.	Min.	Тур.	Max.	Unit
	V _{DD}	Supply Voltage	1	4.5	_	24	V
	I _O	Continuous Output On Current	3	-	-	20	mA
Ī	R _v	Series Resistor	1	_	_	270	Ω

Electrical Characteristics at T_J = –40 °C to +170 °C , V_{DD} = 4.5 V to 24 V, as not otherwise specified Typical Characteristics for T_J = 25 °C and V_{DD} = 12 V

Symbol	Parameter	Pin No.	Min.	Тур.	Max.	Unit	Test Conditions
I _{DD}	Supply Current	1	4.0	5.5	6.8	mA	T _J = 25 °C
I _{DD}	Supply Current over Temperature Range	1	3.0	5.5	7.5	mA	
V _{DDZ}	Overvoltage Protection at Supply	1	-	28.5	32	V	I_{DD} = 25 mA, T _J = 25 °C, t = 20 ms
V _{OZ}	Overvoltage Protection at Output	3	-	28	32	V	$I_{OL} = 25 \text{ mA}, T_J = 25 \text{ °C}, t = 20 \text{ ms}$
V _{OL}	Output Voltage	3	_	180	220	mV	$V_{DD} = 12 \text{ V}, I_{O} = 20 \text{ mA}, T_{J} = 25 \text{ °C}$
V _{OL}	Output Voltage over Temperature Range	3	_	180	400	mV	I _O = 20 mA
I _{OH}	Output Leakage Current	3	_	0.06	1	μΑ	$V_{OH} = 4.5 V24 V,$ $\Delta B < \Delta B_{OFF}, T_J = 25 \ ^{\circ}C$
I _{OH}	Output Leakage Current over Temperature Range	3	_	0.06	10	μΑ	$V_{OH} = 4.5 \text{ V} 24 \text{ V},$ $\Delta B < \Delta B_{OFF}, \text{ T}_J \leq 150 ^{\circ}\text{C}$
f _{osc}	Internal Oscillator Chopper Frequency	_	47	57	78	kHz	
f _{osc}	Internal Oscillator Chopper Fre- quency over Temperature Range	_	42	57	78	kHz	
t _{en(O)}	Enable Time of Output after Setting of V _{DD}	3	-	35	-	μs	$V_{DD} = 12 \text{ V},$ $\Delta B < \Delta B_{ON} - 2\text{mT},$ $\Delta B > \Delta B_{OFF} + 2\text{mT}$
t _r	Output Rise Time	3	_	80	400	ns	V _{DD} = 12 V, RL = 820 Ω, CL = 20 pF
t _f	Output Fall Time	3	_	45	400	ns	V_{DD} = 12 V, RL = 820 Ω , CL = 20 pF
R _{thJSB} case SOT-89A	ase Substrate Backside		-	150	200	K/W	Fiberglass Substrate 30 mm x 10 mm x 1.5mm, pad size see Fig. 7
R _{thJS} case TO-92UA	Thermal Resistance Junction to Soldering Point		_	150	200	K/W	

Magnetic Characteristics at T_J = -40 °C to +170 °C, V_{SUP} = 4.5 V to 24 V, as not otherwise specified, Typical Characteristics for V_{DD} = 12 V

Magnetic flux density values of switching points (Test condition: $B_0 < 10 \text{ mT}$) Positive flux density values refer to the magnetic south pole at the branded side of the package. $\Delta B = B_{S1} - B_{S2}$

Parameter	–40 °C			25 °C			100 °C			170 °C			Unit
	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	
On point ΔB_{ON} B _{S1} – B _{S2} > ΔB_{ON}	0.2	1.07	1.7	0.2	1.0	1.7	0.2	0.93	1.7	0	0.86	1.7	mT
Off point ΔB_{OFF} B _{S1} – B _{S2} < ΔB_{OFF}	-1.7	-0.79	-0.2	-1.7	-0.75	-0.2	-1.7	-0.69	-0.2	-1.7	-0.64	0	mT
Hysteresis $\Delta B_{HYS} = \Delta B_{ON} - \Delta B_{OFF}$	1.2	1.86	2.6	1.2	1.75	2.6	1.2	1.62	2.6	1.0	1.5	2.6	mT

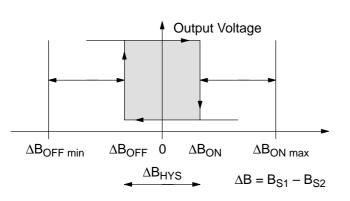


Fig. 6: Definition of switching points and hysteresis

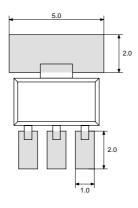
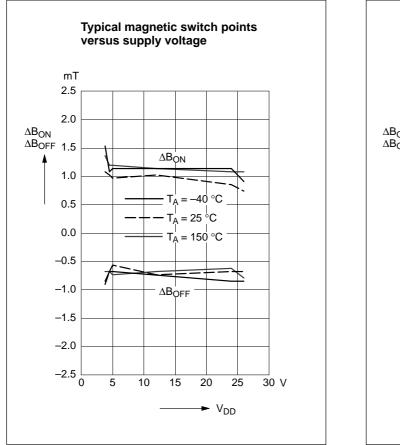
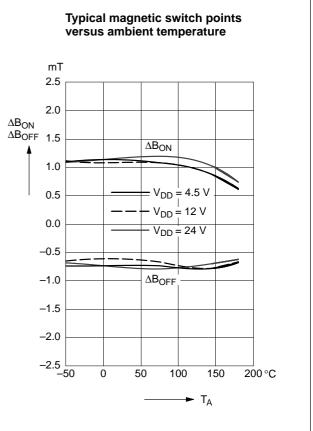
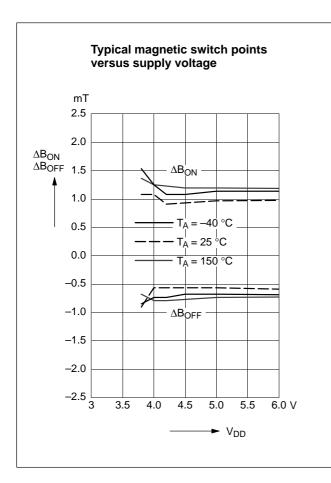


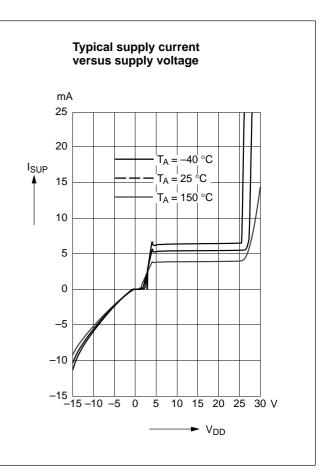
Fig. 7: Recommended pad size SOT-89A Dimensions in mm

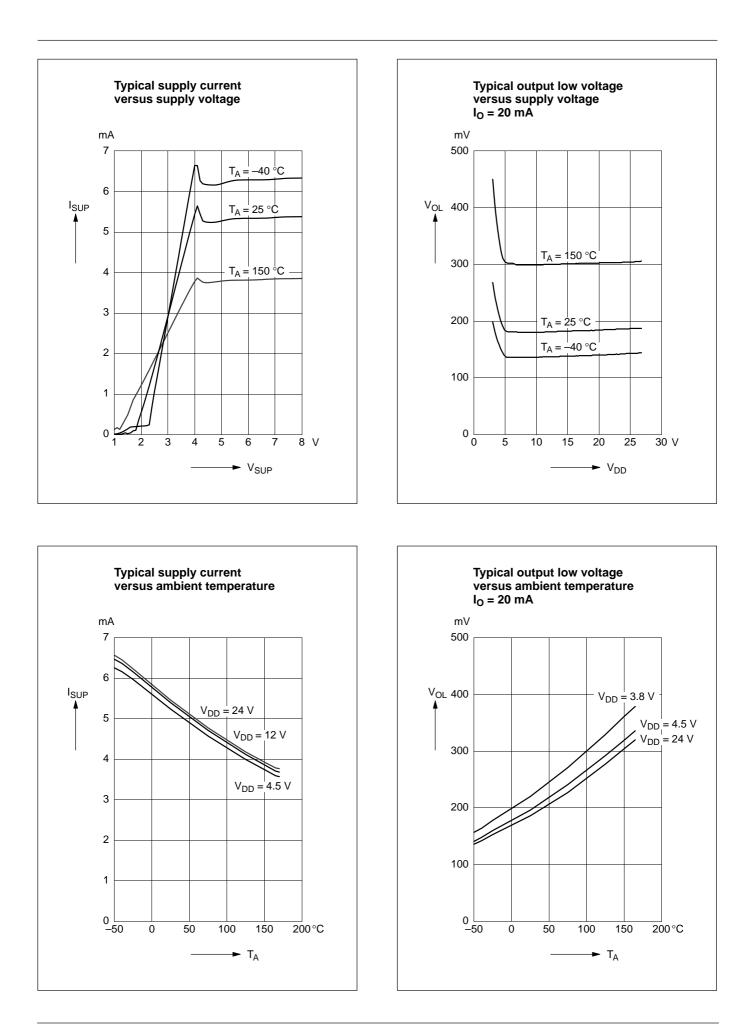
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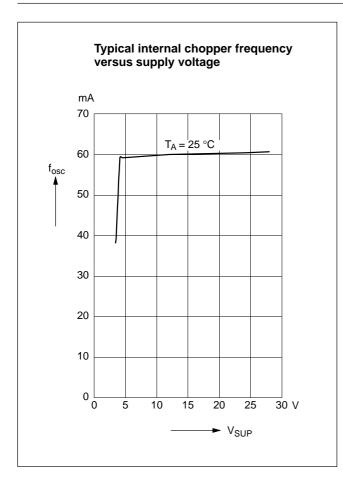


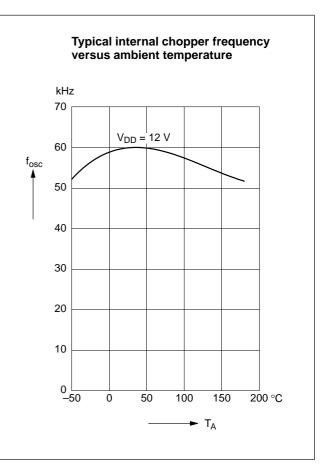


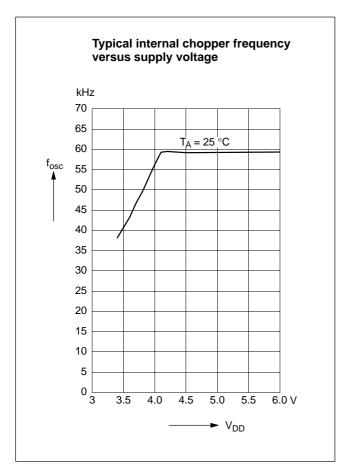


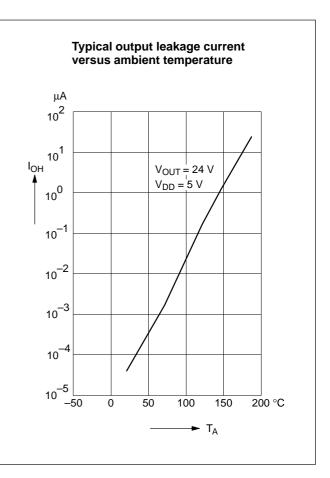


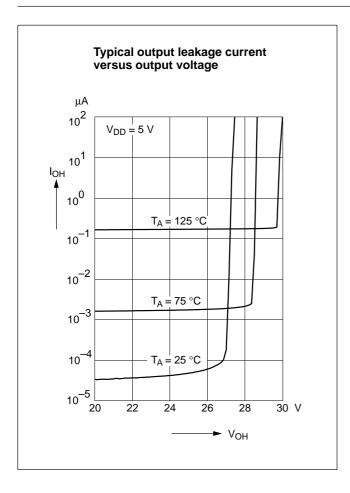
HAL300











Ambient Temperature

Due to the internal power dissipation, the temperature on the silicon chip (junction temperature T_J) is higher than the temperature outside the package (ambient temperature T_A).

$$T_J = T_A + \Delta T$$

At static conditions, the following equations are valid:

- for SOT-89A: $\Delta T = I_{DD} * V_{DD} * R_{thJSB}$
- for TO-92UA: $\Delta T = I_{DD} * V_{DD} * R_{thJA}$

For typical values, use the typical parameters. For worst case calculation, use the max. parameters for I_{DD} and R_{th} , and the max. value for V_{DD} from the application.

Test Circuits for Electromagnetic Compatibility Test pulses V_{EMC} corresponding to DIN 40839.

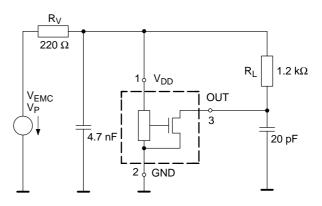


Fig. 8: Test circuit 2: test procedure for class A

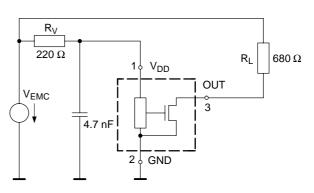


Fig. 9: Test circuit 1: test procedure for class C

Application Note

For electromagnetic immunity, it is recommended to apply a 4.7 nF capacitor between V_{DD} (pin 1) and Ground (pin 2).

For automotive applications, a 220 Ω series resistor to pin 1 is recommended.

Because of the I_{DD} peak at 4.1 V, the series resistor should not be greater than 270 $\Omega.$

The series resistor and the capacitor should be placed as close as possible to the IC.

Interferences conducted along supply lines in 12 V onboard systems

Product standard: DIN 40839 part 1

Pulse	Level	U _s in V	Test circuit	Pulses/ Time	Function Class	Remarks
1	IV	-100	1	5000	С	5 s pulse interval
2	IV	100	1	5000	С	0.5 s pulse interval
За	IV	-150	2	1 h	A	
3b	IV	100	2	1h	A	
4	IV	-7	2	5	A	
5	IV	86.5	1	10	С	10 s pulse interval

Electrical transient transmission by capacitive and inductive coupling via lines other than the supply lines

Product standard: DIN 40839 part 3

Pulse	Level	U _s in V	Test circuit	Pulses/ Time	Function Class	Remarks
1	IV	-30	2	500	А	5 s pulse interval
2	IV	30	2	500	А	0.5 s pulse interval
3a	IV	-60	2	10 min	А	
3b	IV	40	2	10 min	А	

Radiated Disturbances

Product standard: DIN 40839 part4

Test Conditions

- Temperature: Room temperature (22...25 °C)
- Supply voltage: 13 V
- Lab Equipment: TEM cell 220 MHz (VW standard) with adaptor board 455 mm, device 80 mm over ground
- Frequency range: 5...220 MHz; 1 MHz steps
- Test circuit 2 with RL = 1.2 $k\Omega$

Tested Devices and Results

Туре	Field strength	Modulation	Result				
HAL 300	> 200 V/m	1 kHz 80 %	output voltage stable on the level high or low ¹⁾				
$^{1)}$ low level $<$ 0.4 V, high level $>$ 90% of V_{DD}							

Data Sheet History

1. Preliminary data sheet: "HAL300 Differential Hall Effect Sensor IC", Sept. 30, 1992, 6251-345-1PD. First release of the preliminary data sheet.

2. Preliminary data sheet: "HAL300 Differential Hall Effect Sensor IC", Nov. 6, 1992, 6251-345-2PD. Second release of the preliminary data sheet.

3. Preliminary data sheet: "HAL300 Differential Hall Effect Sensor IC", June 14, 1994, 6251-345-3PD. Third release of the preliminary data sheet.

4. Preliminary data sheet: "HAL300 Differential Hall Effect Sensor IC", May 7, 1997, 6251-345-4PD. Fourth release of the preliminary data sheet. Major changes:

- outline dimensions for TO-92UA package changed
- page 10: "Ambient Temperature"
- oscillator frequency limits changed
- hysteresis limits changed

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